

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	57	(orient\$4 near platinum)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:43
L2	1	(orient\$4 near platinum) and temperature and nucleat\$4 and gas and "metal oxide" and "BSTO"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:45
L3	1	(orient\$4 near platinum) and temperature and nucleat\$4 and gas and "metal oxide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:46
L4	3	(orient\$4 near platinum) and temperature and nucleat\$4 and gas	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/16 10:46
S1	0	"capacitor electrode" and (substrate or wafer or semiconductor) and (gas near8 temp\$4) and ((first or primary or one or singl\$4) same (second or two or plural\$4)) and (oxide or titanate) and barium and strontium and titanium and oxygen and "BSTO" and seed and grow and platinum and crystalline	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:51
S2	33932817	"capacitor electrode" and (substrate or wafer or semiconductor) and (gas near8 temp\$4) and ((first or primary or one or singl\$4) same (second or two or plural\$4)) and (oxide or titanate) and barium and strontium and titanium and oxygen and "BSTO" a	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:52

S3	0	"capacitor electrode" and (substrate or wafer or semiconductor) and (gas near8 temp\$4) and ((first or primary or one or singl\$4) same (second or two or plural\$4)) and (oxide or titanate) and barium and strontium and titanium and oxygen and "BSTO"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:52
S4	1	"capacitor electrode" and (substrate or wafer or semiconductor) and (gas near8 temp\$4) and ((first or primary or one or singl\$4) same (second or two or plural\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:53
S5	284	electrode and (substrate or wafer or semiconductor) and (gas near8 temp\$4) and ((first or primary or one or singl\$4) same (second or two or plural\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:53
S6	0	electrode and (substrate or wafer or semiconductor) and (gas near8 temp\$4) and ((first or primary or one or singl\$4) same (second or two or plural\$4)) and "BSTO"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:53
S7	13	electrode and (substrate or wafer or semiconductor) and (gas near8 temp\$4) and ((first or primary or one or singl\$4) same (second or two or plural\$4)) and barium and strontium and oxide and titanium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:54
S8	9	electrode and (substrate or wafer or semiconductor) and (gas near8 temp\$4) and ((first or primary or one or singl\$4) same (second or two or plural\$4)) and barium and strontium and oxide and titanium and crystalline	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:55
S9	81	electrode and (substrate or wafer or semiconductor) and (dielectric near8 gas) and (temperature or thermal) and ((first or primary or one or singl\$4) same (second or two or plural\$4)) and barium and strontium and oxide and titanium and crystalline	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:56

S10	61	electrode and (substrate or wafer or semiconductor) and (dielectric near8 gas) and (temperature or thermal) and ((first or primary or one or singl\$4) same (second or two or plural\$4)) and barium and strontium and oxide and titanium and crystalline and titanate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:56
S11	31	electrode and (substrate or wafer or semiconductor) and (dielectric near8 gas) and (temperature or thermal) and ((first or primary or one or singl\$4) same (second or two or plural\$4)) and barium and strontium and oxide and titanium and crystalline and titanate and conductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:56
S12	30	electrode and (substrate or wafer or semiconductor) and (dielectric near8 gas) and (temperature or thermal) and ((first or primary or one or singl\$4) same (second or two or plural\$4)) and barium and strontium and oxide and titanium and crystalline and titanate and conductor and oxygen	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:57
S13	0	electrode and (substrate or wafer or semiconductor) and (dielectric near8 gas) and (temperature or thermal) and ((first or primary or one or singl\$4) same (second or two or plural\$4)) and barium and strontium and oxide and titanium and crystalline and titanate and conductor and oxygen and seed	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:57
S14	29	electrode and (substrate or wafer or semiconductor) and (dielectric near8 gas) and (temperature or thermal) and ((first or primary or one or singl\$4) same (second or two or plural\$4)) and barium and strontium and oxide and titanium and crystalline and titanate and conductor and oxygen and time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:57
S15	15	electrode and (substrate or wafer or semiconductor) and (dielectric near8 gas) and (temperature or thermal) and ((first or primary or one or singl\$4) same (second or two or plural\$4)) and barium and strontium and oxide and titanium and crystalline and titanate and conductor and oxygen and time and capacitance	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:57

S16	2	electrode and (substrate or wafer or semiconductor) and (dielectric near8 gas) and (temperature or thermal) and (((first or primary or one or singl\$4) same (second or two or plural\$4)) and barium and strontium and oxide and titanium and crystalline and titanate and conductor and oxygen and time and capacitance and nucleat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 08:05
S17	513	"BSTO"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:00
S18	363	"BSTO" and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:00
S19	4	"BSTO" and electrode and (substrate or wafer or semiconductor) and (((first or one or primary) near gas) same ((second or plural\$4 or two) near gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:03
S20	4	"BSTO" and electrode and (substrate or wafer or semiconductor) and (((first or one or primary) near gas) same ((second or plural\$4 or two) near gas)) and temperature	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:31
S21	1	"BSTO" and electrode and (substrate or wafer or semiconductor) and (((first or one or primary) near gas) same ((second or plural\$4 or two) near gas)) and temperature and crystalline	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:04
S22	0	"BSTO" and electrode and (substrate or wafer or semiconductor) and (((first or one or primary) near gas) same ((second or plural\$4 or two) near gas)) and temperature and crystalline and conductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:04

S23	0	"BSTO" and electrode and (substrate or wafer or semiconductor) and (((first or one or primary) near gas) same ((second or plural\$4 or two) near gas)) and temperature and crystalline and (metal near oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:04
S24	1348	"BSTO" and barium and strontium and titanium and oxygen and electrode and (semiconductor or wafer or substrate) and (heat or thermal) and temperature seed and nucleat\$4 and "metal oxide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:35
S25	48	"BSTO" and barium and strontium and titanium and oxygen and electrode and (semiconductor or wafer or substrate) and (heat or thermal) and temperature seed and nucleat\$4 and "metal oxide" and (((first or one or primary) near gas) same ((second or plural\$4 or two) near gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:36
S26	42	"BSTO" and barium and strontium and titanium and oxygen and electrode and (semiconductor or wafer or substrate) and (heat or thermal) and temperature seed and nucleat\$4 and "metal oxide" and (((first or one or primary) near gas) same ((second or plural\$4 or two) near gas)) and conductor and time	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:36
S27	41	"BSTO" and barium and strontium and titanium and oxygen and electrode and (semiconductor or wafer or substrate) and (heat or thermal) and temperature seed and nucleat\$4 and "metal oxide" and (((first or one or primary) near gas) same ((second or plural\$4 or two) near gas)) and conductor and time and grow	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 10:30
S28	5	"6207584"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 08:06

S29	41	"BSTO" and barium and strontium and titanium and oxygen and electrode and (semiconductor or wafer or substrate) and (heat or thermal) and temperature seed and nucleat\$4 and "metal oxide" and (((first or one or primary) near gas) same ((second or plural\$4 or two) near gas)) and conductor and time and grow and platinum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 10:31
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